BLC8G21LS-160AV

Power LDMOS transistor

Rev. 1 — 12 August 2014 Product data sheet

1. Product profile

1.1 General description

160 W LDMOS transistor for base station applications at frequencies from 1805 MHz to 2025 MHz.

Table 1. Typical performance

Typical RF performance at T_{case} = 25 °C in a Doherty demo board.

Test signal	f	I_{Dq}	V_{DS}	$P_{L(AV)}$	G_p	η_D	ACPR
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	1805 to 1880	350	28	22	16	49	–30 [1]
1-carrier W-CDMA	1880 to 2025	350	28	22	15.5	47	–30 [1]

[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF.

1.2 Features and benefits

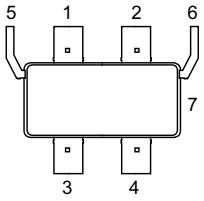
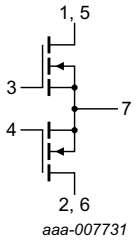
- Designed for broadband operation (1805 MHz to 2025 MHz)
- Decoupling leads to enable improved video bandwidth
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Internally matched for ease of use
- High power gain
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- RF power amplifiers for base station and multi-carrier applications in the 1805 MHz to 2025 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain1 (main)		
2	drain2 (peak)		
3	gate1 (main)		
4	gate2 (peak)		
5	video decoupling (main)		
6	video decoupling (peak)		
7	source [1]		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLC8G21LS-160AV	-	air cavity plastic earless flanged package; 6 leads	SOT1275-1

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		–0.5	+13	V
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature	[1]	-	225	°C

[1] Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j\text{-}case)}$	thermal resistance from junction to case	T_{case} = 80 °C; V_{DS} = 28 V; I_{Dq} = 400 mA		
		P_L = 23 W	0.371	K/W
		P_L = 89 W	0.278	K/W

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6. Characteristics

Table 6. DC characteristics

T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Main device						
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.72 mA	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_D = 72 mA	1.5	1.9	2.3	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 28 V; I_D = 432 mA	1.6	2.1	2.4	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	1.4	µA
I_{DSX}	drain cut-off current	V_{GS} = $V_{GS(th)}$ + 3.75 V; V_{DS} = 10 V	-	14	-	A
I_{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	140	nA
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 72 mA	-	0.60	-	S
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = $V_{GS(th)}$ + 3.75 V; I_D = 2.52 A	-	205	323	mΩ
Peak device						
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 1.1 mA	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_D = 110 mA	1.5	1.9	2.3	V
V_{GSq}	gate-source quiescent voltage	V_{DS} = 28 V; I_D = 660 mA	1.6	2.0	2.4	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	1.4	µA
I_{DSX}	drain cut-off current	V_{GS} = $V_{GS(th)}$ + 3.75 V; V_{DS} = 10 V	-	20	-	A
I_{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	140	nA
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 110 mA	-	0.97	-	S
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = $V_{GS(th)}$ + 3.75 V; I_D = 3.85 A	-	145	215	mΩ

Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 - 64 DPCH; f_1 = 1880 MHz; f_2 = 2025 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 200 mA (main); $V_{GS(amp)peak}$ = 0.5 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at 1880 MHz to 2025 MHz.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	$P_{L(AV)}$ = 22.5 W	13.8	15	-	dB
RL_{in}	input return loss	$P_{L(AV)}$ = 22.5 W	-	–10	–6	dB
η_D	drain efficiency	$P_{L(AV)}$ = 22.5 W	40	45	-	%
ACPR	adjacent channel power ratio	$P_{L(AV)}$ = 22.5 W	-	–30	–25	dBc

Table 8. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 - 64 DPCH; f = 2025 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 200 mA (main); $V_{GS(amp)peak}$ = 0.5 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at 1880 MHz to 2025 MHz.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
PAR_O	output peak-to-average ratio	$P_{L(AV)}$ = 60 W	4.3	4.9	-	dB
$P_{L(M)}$	peak output power		158	185	-	W

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7. Test information

7.1 Ruggedness in Doherty operation

The BLC8G21LS-160AV is capable of withstanding a load mismatch corresponding to a VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 200 mA (main); $V_{GS(amp)peak}$ = 0.5 V; P_L = 120 W (CW); f = 1880 MHz.

7.2 Impedance information

Table 9. Typical impedance of main device

Measured load-pull data of main device; I_{Dq} = 450 mA (main); V_{DS} = 28 V.

f	Z_S [1]	Z_L [1]	P_L [2]	η_D [2]	G_p [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
Maximum power load					
1805	1.63 – j7.04	2.69 – j7.69	87.05	55.92	16.44
1880	2.43 – j7.93	2.69– j7.69	84.00	55.41	16.40
1920	3.64 – j9.19	3.32 – j8.33	82.41	58.81	17.29
2025	9.22 – j10.74	2.69 – j7.69	83.16	60.51	17.28
Maximum drain efficiency load					
1805	1.63 – j7.04	7.07– j5.17	55.89	69.34	19.16
1880	2.43 – j7.93	5.49 – j4.59	55.05	68.21	19.14
1920	3.64 – j9.19	4.63 – j4.53	54.27	67.40	18.94
2025	9.22 – j10.74	3.29 – j5.36	55.68	65.66	18.96

[1] Z_S and Z_L defined in Figure 1.

[2] at 3 dB gain compression.

Table 10. Typical impedance of peak device

Measured load-pull data of peak device; I_{Dq} = 600 mA (peak); V_{DS} = 28 V.

f	Z_S [1]	Z_L [1]	P_L [2]	η_D [2]	G_p [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
Maximum power load					
1805	1.11 – j6.63	3.23 – j7.06	126.00	56.38	16.26
1880	1.60 – j7.94	3.23 – j7.06	122.98	55.66	16.28
1920	3.45 – j8.58	3.23 – j7.06	120.56	55.34	16.18
2025	5.33 – j7.56	3.97 – j7.59	128.56	58.56	16.97
Maximum drain efficiency load					
1805	1.11 – j6.63	5.83 – j3.19	80.08	66.92	18.77
1880	1.60 – j7.94	4.65 – j3.75	84.85	65.61	18.59
1920	3.45 – j8.58	3.94 – j3.76	81.80	64.85	18.37
2025	5.33 – j7.56	3.24 – j4.34	82.20	65.52	18.89

[1] Z_S and Z_L defined in Figure 1.

[2] at 3 dB gain compression.

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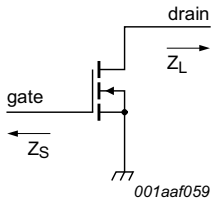


Fig 1. Definition of transistor impedance

7.3 Recommended impedances for Doherty design

Table 11. Typical impedance of main device at 1 : 1 load

Measured load-pull data of main device; I_{Dq} = 450 mA (main); V_{DS} = 28 V.

f	Z_S [1]	Z_L [1]	P_L [2]	η_D [3]	G_p [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
1805	1.63 – j7.04	4.46 – j6.76	48.9	40.0	21.0
1880	2.43 – j7.93	4.46 – j6.76	48.6	41.0	21.3
1920	3.64 – j9.19	4.46 – j6.76	48.6	41.0	21.3
2025	9.22 – j10.74	3.23 – j7.06	48.7	41.0	21.1

[1] Z_S and Z_L defined in Figure 1.

[2] at 3 dB gain compression.

[3] at $P_{L(AV)}$ = 43.5 dBm.

Table 12. Typical impedance of main device at 1 : 2.5 load

Measured load-pull data of main device; I_{Dq} = 450 mA (main); V_{DS} = 28 V.

f	Z_S [1]	Z_L [1]	P_L [2]	η_D [3]	G_p [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
1805	1.63 – j7.04	7.87 – j2.50	46.2	49.5	22.2
1880	2.43 – j7.93	7.43 – j2.21	45.8	53.1	22.9
1920	3.64 – j9.19	7.43 – j2.21	45.8	53.1	22.9
2025	9.22 – j10.74	3.94 – j3.76	45.9	54.6	22.9

[1] Z_S and Z_L defined in Figure 1.

[2] at 3 dB gain compression.

[3] at $P_{L(AV)}$ = 43.5 dBm.

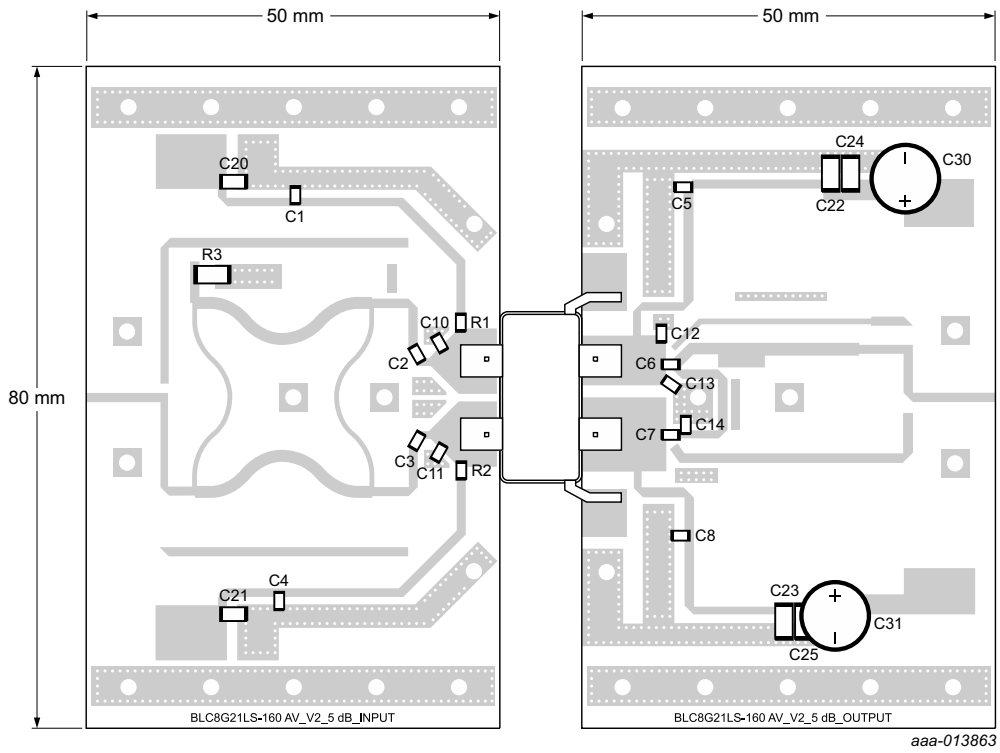
7.4 VBW in Doherty operation

The BLC8G21LS-160AV shows 110 MHz (typical) video bandwidth in Doherty demo board in 1880 MHz at V_{DS} = 28 V; I_{Dq} = 200 mA and $V_{GS(amp)peak}$ = 0.5 V.

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7.5 Test circuit



Printed-Circuit Board (PCB): Rogers RO4350B; thickness = 0.508 mm; thickness copper plating = 35 μm.

See Table 13 for a list of components.

Fig 2. Component layout for test circuit

Table 13. List of components

See Figure 2 for component layout.

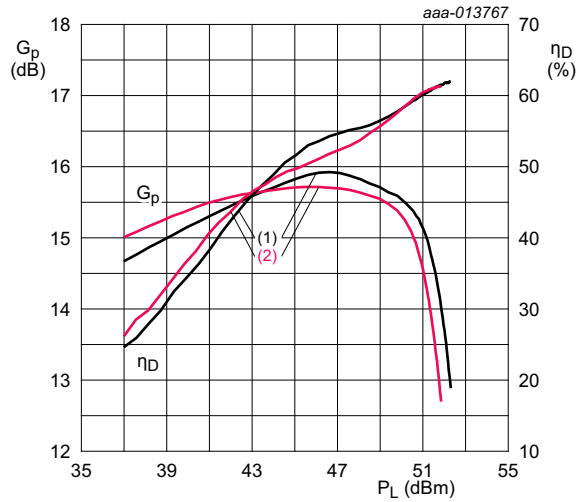
Component	Description	Value	Remarks
C1, C2, C3, C4, C5, C6, C7, C8	multilayer ceramic chip capacitor	22 pF	
C10	multilayer ceramic chip capacitor	0.3 pF	
C11	multilayer ceramic chip capacitor	0.8 pF	
C12	multilayer ceramic chip capacitor	0.5 pF	
C13	multilayer ceramic chip capacitor	0.7 pF	
C14	multilayer ceramic chip capacitor	1.1 pF	
C20, C21, C22, C23	multilayer ceramic chip capacitor	1 μF, 50 V	
C24, C25	multilayer ceramic chip capacitor	10 μF, 50 V	
C30, C31	electrolytic capacitor	2200 μF, 50 V	
R1, R2	SMD resistor	5.1 Ω	
R3	wire resistor	50 Ω	

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7.6 Graphical data

7.6.1 Pulsed CW

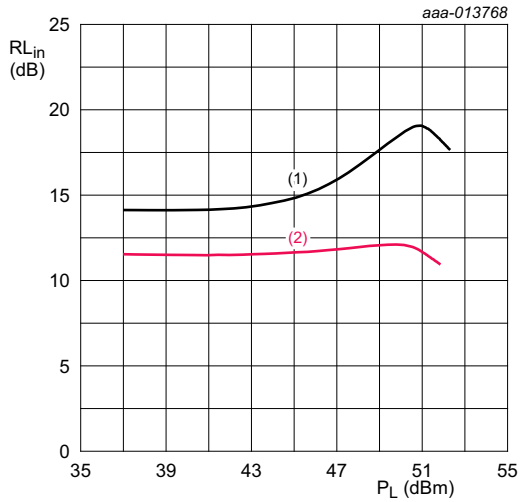


V_{DS} = 28 V; I_{Dq} = 200 mA (main device); $V_{GS(amp)peak}$ = 0.5 V.

(1) f = 1880 MHz

(2) f = 2025 MHz

Fig 3. Power gain and drain efficiency as function of output power; typical values



V_{DS} = 28 V; I_{Dq} = 200 mA (main device); $V_{GS(amp)peak}$ = 0.5 V.

(1) f = 1880 MHz

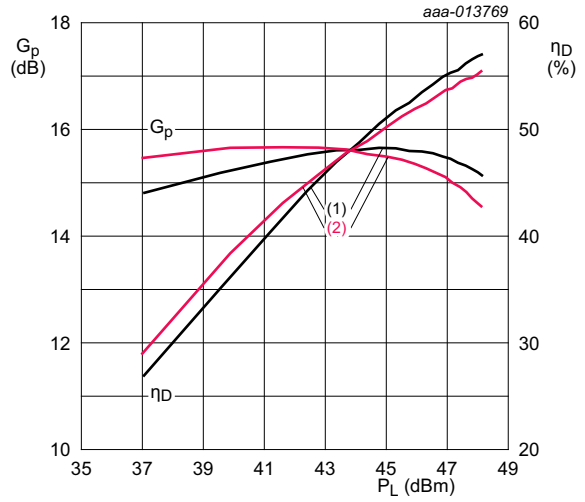
(2) f = 2025 MHz

Fig 4. Input return loss as a function of output power; typical values

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7.6.2 1-Carrier W-CDMA

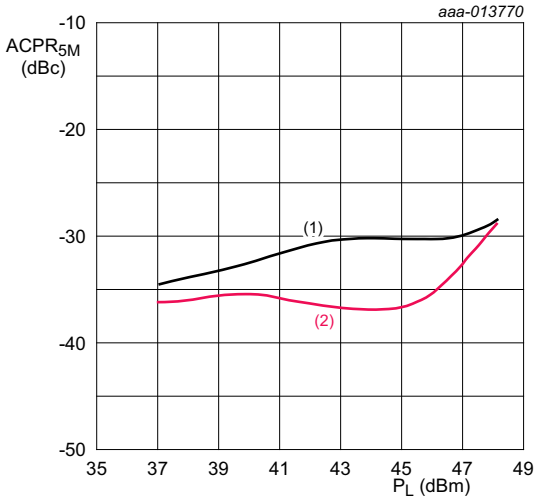


V_{DS} = 28 V; I_{Dq} = 200 mA (main device); $V_{GS(amp)peak}$ = 0.5 V.

(1) f = 1880 MHz

(2) f = 2025 MHz

Fig 5. Power gain and drain efficiency as function of output power; typical values

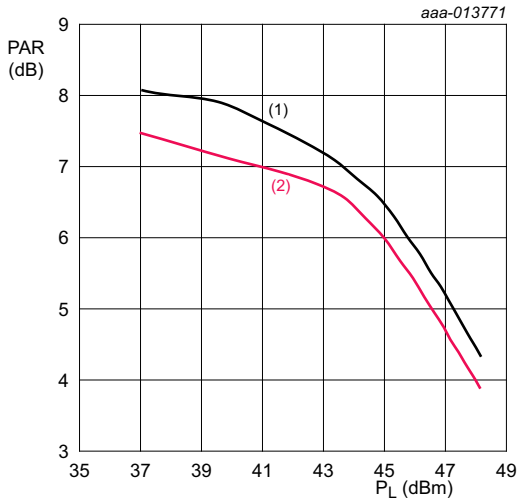


V_{DS} = 28 V; I_{Dq} = 200 mA (main device); $V_{GS(amp)peak}$ = 0.5 V.

(1) f = 1880 MHz

(2) f = 2025 MHz

Fig 6. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



V_{DS} = 28 V; I_{Dq} = 200 mA (main device); $V_{GS(amp)peak}$ = 0.5 V.

(1) f = 1880 MHz

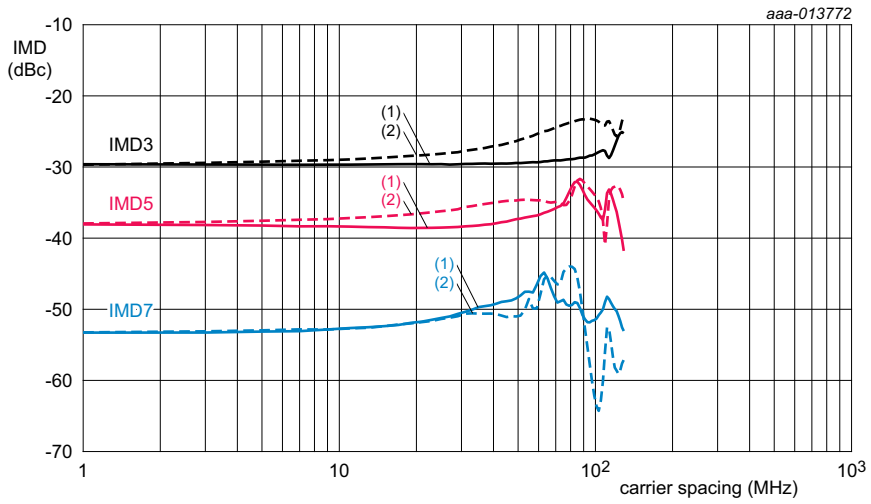
(2) f = 2025 MHz

Fig 7. Peak-to-average power ratio as a function of output power; typical values

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7.6.3 2-Tone VBW



V_{DS} = 28 V; I_{Dq} = 200 mA (main device); $V_{GS(amp)peak}$ = 0.5 V; f = 1880 MHz.

(1) IMD low

(2) IMD high

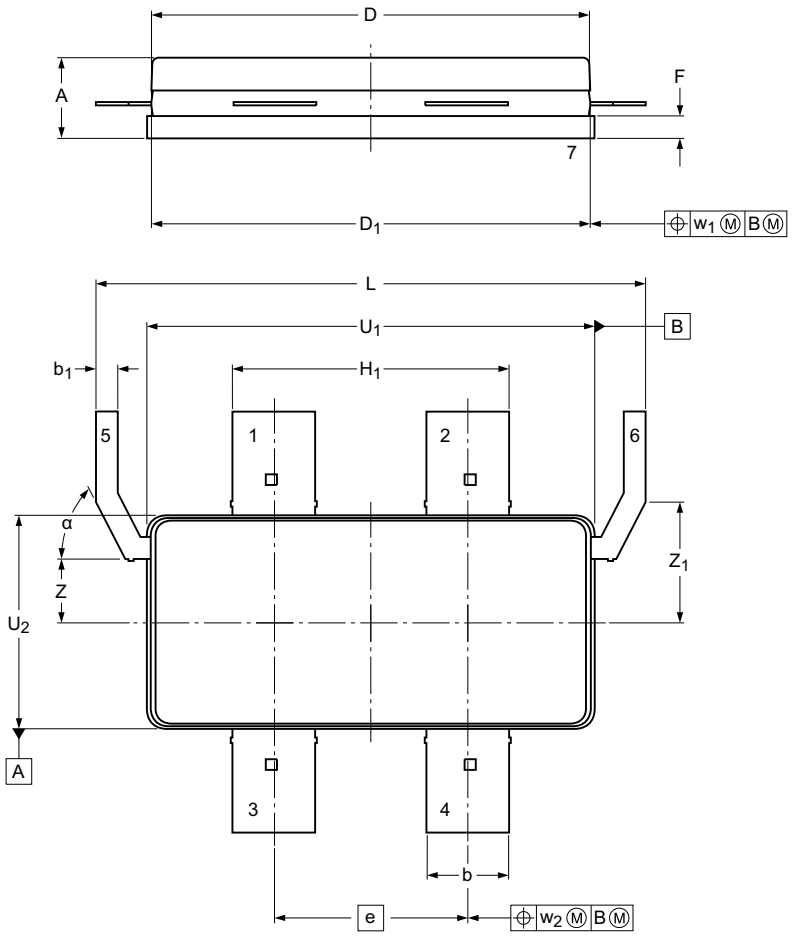
Fig 8. VBW capability in Doherty demo board

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8. Package outline

Air cavity plastic earless flanged package; 6 leads **SOT1275-1**



v	w1	w2
0.5	0.5	0.5

Dimensions (mm dimensions are derived from the original inch dimensions)

Unit		A	b	b_1	c	D	D_1	E	E_1	e	F	H	H_1	L	Q	U_1	U_2	Z	Z_1	α
mm	max	4.01	3.94	1.14	0.178	20.42	20.37	9.80	9.75		1.14	19.53	12.80	25.40	1.68	20.70	9.91	3.67	5.79	65°
	nom									8.89										
	min	3.40	3.68	0.89	0.127	20.12	20.17	9.50	9.55		0.94	19.33	12.60	25.20	1.45	20.50	9.70	3.17	5.29	61°

sot1275-1_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1275-1						~~13-10-08~~ 14-01-13

Fig 9. Package outline SOT1275-1

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9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 14. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VBW	Video BandWidth
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 15. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC8G21LS-160AV v.1	20140812	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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